

Vladimir A Kulbachinskii

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Doping Nature of Group V Elements in ZnO Single Crystals Grown from Melts at High Pressure. <i>Crystal Growth and Design</i> , 2022, 22, 2452-2461.	1.4	5
2	“Thermoelectrical properties and Shubnikov de Haas effect in single crystals $Sb_{2-x}Cu_xTe_3$. <i>Materials Today: Proceedings</i> , 2021, 44, 3439-3444.	0.9	1
3	Effect of magnesium doping on thermoelectric and magnetic properties of copper chromite ceramic samples. <i>Materials Today: Proceedings</i> , 2021, 44, 3511-3515.	0.9	0
4	Sb_2Te_3 /graphite nanocomposite: A comprehensive study of thermal conductivity. <i>Journal of Materiomics</i> , 2021, 7, 545-555.	2.8	5
5	Preparation and superconducting behavior of triammonium fulleride. <i>Carbon</i> , 2021, 182, 51-56.	5.4	1
6	Evolution to an anisotropic band structure caused by Sn doping in $Bi_{1.995}Sn_{0.005}Te_3$ single crystals. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 035705.	0.7	1
7	Superconductivity in alkali-doped fullerides with wood’s metal and heterofullerides with two different alkali metals $A^{(1)}A^{(2)}MC_{60}$. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , 2020, 28, 168-172.	1.0	2
8	Shubnikov de Haas Effect and Electrophysical Properties of the Topological Insulator $Sb_2-xCu_xTe_3$. <i>Journal of Experimental and Theoretical Physics</i> , 2019, 128, 926-931.	0.2	2
9	Creation of Acceptor Centers in ZnO Single Crystals by Annealing in Sb Vapor. <i>Journal of Physical Chemistry C</i> , 2019, 123, 20769-20773.	1.5	3
10	Thermoelectric Properties of Sb_2Te_3 -Based Nanocomposites with Graphite. <i>Semiconductors</i> , 2019, 53, 638-640.	0.2	6
11	Nanostructuring and Creation of Nanocomposites as a Promising Way to Increase Thermoelectric Efficiency. <i>Nanotechnologies in Russia</i> , 2019, 14, 334-345.	0.7	4
12	Superconductivity, Magnetoresistance, Magnetic Anomaly and Crystal Structure of New Phases of Topological Insulators Bi_2Se_3 and Sb_2Te_3 . <i>Journal of Physics: Conference Series</i> , 2018, 969, 012152.	0.3	3
13	Magnetotransport properties of FeSe in fields up to 50 T. <i>Journal of Magnetism and Magnetic Materials</i> , 2018, 459, 221-225.	1.0	2
14	Stress-controlled thermoelectric module for energy harvesting and its application for the significant enhancement of the power factor of Bi_2Te_3 -based thermoelectrics. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 025501.	1.3	18
15	Superparamagnetic behavior of MOCVD grown ZnO:Co films. <i>EPJ Web of Conferences</i> , 2018, 185, 06009.	0.1	1
16	Quantum effects in magnetotransport of InGaAs quantum wells with remote Mn impurities. <i>EPJ Web of Conferences</i> , 2018, 185, 06007.	0.1	0
17	Effect of thallium doping on the mobility of electrons in Bi_2Se_3 and holes in Sb_2Te_3 . <i>Semiconductors</i> , 2016, 50, 869-875.	0.2	3
18	Superconductivity of Fullerides with Composition AGa_xC_{60} and $AGa_xM_yC_{60}$ ($A = K, Rb; M = In, Sn, Bi$). <i>Journal of Low Temperature Physics</i> , 2016, 185, 502-507.	0.6	2

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19	Effect of Co Doping on the Galvanomagnetic Properties of ZnO Thin Films. Solid State Phenomena, 2015, 233-234, 713-716.	0.3	0
20	Influence of buffer-layer construction and substrate orientation on the electron mobilities in metamorphic In _{0.70} Al _{0.30} As/In _{0.76} Ga _{0.24} As/In _{0.70} Al _{0.30} As structures on GaAs substrates. Semiconductors, 2015, 49, 921-929.	0.2	6
21	Anomalous Hall Effect in 2D DMS. Solid State Phenomena, 2015, 233-234, 109-112.	0.3	1
22	Superconductivity of heterofullerides with one or two atoms of the alkali metals and gallium, indium, bismuth or tin. Polyhedron, 2015, 102, 664-667.	1.0	8
23	Experimental Determination of the Subband Electron Effective Mass in InGaAs/InAlAs HEMT-structures by the Shubnikov-de Haas Effect at Two Temperatures. Physics Procedia, 2015, 72, 425-430.	1.2	6
24	The Shubnikov-de Haas effect and thermoelectric properties of TI-doped Sb ₂ Te ₃ and Bi ₂ Se ₃ . Semiconductors, 2015, 49, 767-773.	0.2	8
25	Experimental determination of the electron effective masses and mobilities in each dimensionally-quantized subband in an In _x Ga _{1-x} As quantum well with InAs inserts. Semiconductors, 2015, 49, 199-208.	0.2	15
26	Superconductivity in bulk polycrystalline metastable phases of Sb ₂ Te ₃ and Bi ₂ Te ₃ quenched after high-pressure-high-temperature treatment. Chemical Physics Letters, 2015, 631-632, 97-102.	1.2	20
27	Enhanced power factor and high-pressure effects in (Bi,Sb) ₂ (Te,Se) ₃ thermoelectrics. Applied Physics Letters, 2015, 106, .	1.5	41
28	Weak superconductivity in the surface layer of a bulk single-crystal boron-doped diamond. Europhysics Letters, 2014, 108, 67014.	0.7	9
29	Persistent photoconductivity and electron mobility in In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As/InP quantum-well structures. Semiconductors, 2013, 47, 935-942.	0.2	5
30	Electron mobilities in isomorphous In _{0.53} Ga _{0.47} As quantum wells on InP substrates. Journal of Experimental and Theoretical Physics, 2013, 116, 755-759.	0.2	3
31	Enhancement of Electron Mobility and Photoconductivity in Quantum Well In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As/InP Substrate. Acta Physica Polonica A, 2013, 123, 345-348.	0.2	0
32	Synthesis and thermoelectric properties of Re ₃ As _{6.6} In _{0.4} with Ir ₃ Ge ₇ crystal structure. Beilstein Journal of Nanotechnology, 2013, 4, 446-452.	1.5	0
33	Influence of Magnetic Impurities on Thermoelectric Capabilities of Bi ₂ Te ₃ , Sb ₂ Te ₃ , and Bi ₂ Se ₃ . Solid State Phenomena, 2012, 190, 558-561.	0.3	0
34	Thermoelectric properties of Bi ₂ Te ₃ , Sb ₂ Te ₃ and Bi ₂ Se ₃ single crystals with magnetic impurities. Journal of Solid State Chemistry, 2012, 193, 47-52.	1.4	35
35	Influence of Sn on the thermoelectric properties of (Bi _x Sb _{1-x}) ₂ Te ₃ single crystals. Journal of Solid State Chemistry, 2012, 193, 83-88.	1.4	7
36	Composites of Bi ₂ Sb Te ₃ nanocrystals and fullerene molecules for thermoelectricity. Journal of Solid State Chemistry, 2012, 193, 64-70.	1.4	33

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37	On the electronic structure and thermoelectric properties of BiTeBr and BiTeI single crystals and of BiTeI with the addition of BiI ₃ and CuI. Journal of Solid State Chemistry, 2012, 193, 154-160.	1.4	31
38	Effect of the nanostructure on room temperature ferromagnetism and resistivity of undoped ZnO thin films grown by chemical vapor deposition. Thin Solid Films, 2012, 520, 4580-4585.	0.8	20
39	Superhard Superconductive Composite Materials Obtained by High-Pressure-High-Temperature Sintering. , 2011, , .		0
40	Thermoelectric properties of bismuth telluride nanocomposites with fullerene. Semiconductors, 2011, 45, 1194-1198.	0.2	17
41	Anomalously low thermal conductivity and thermoelectric properties of new cationic clathrates in the Sn-In-As-I system. Semiconductors, 2011, 45, 1399-1403.	0.2	10
42	Synthesis, Crystal Structure, and Thermoelectric Properties of Clathrates in the Sn-In-As-I System. Zeitschrift Fur Anorganische Und Allgemeine Chemie, 2011, 637, 2059-2067.	0.6	9
43	Anomalous enhancement of the thermoelectric power in gallium-doped p-(Bi ^{1-x} Sb ^x) ₂ Te ₃ single crystals. Journal of Experimental and Theoretical Physics, 2010, 110, 618-621.	0.2	3
44	Galvanomagnetic and thermoelectric properties of BiTeBr and BiTeI single crystals and their electronic structure. Semiconductors, 2010, 44, 1548-1553.	0.2	20
45	Anomalous increase of the thermopower and thermoelectric figure of merit in Ga-doped p-(Bi _{0.5} Sb _{0.5}) ₂ Te ₃ single crystals. Physics of the Solid State, 2010, 52, 1830-1835.	0.2	15
46	Magnetic and structural anomalies of NaC ₆₀ (n = 2, 3). Open Physics, 2010, 8, .	0.8	5
47	Calculation of Carrier Scattering in Mn-doped InGaAs Quantum Well with Hole-mediated Ferromagnetism. , 2010, , .		2
48	Superconductivity of Fullerides A _n Hg _x C ₆₀ (A = K,Rb,Cs; n = 2,3) Synthesized from Amalgams. Fullerenes Nanotubes and Carbon Nanostructures, 2010, 18, 381-385.	1.0	9
49	THE THERMODYNAMIC, TRANSPORT AND MAGNETOTRANSPORT PROPERTIES OF Mn-DOPED GaAs/InGaAs/GaAs QUANTUM WELL WITH FERROMAGNETISM. International Journal of Modern Physics B, 2009, 23, 3596-3601.	1.0	2
50	Thermal, transport, and magnetotransport properties of free charge carriers in Mn-doped structures with a GaAs/InGaAs/GaAs quantum well. Journal of Experimental and Theoretical Physics, 2009, 109, 117-127.	0.2	1
51	Resonant level formed by tin in $Bi_{1-x}Mn_x$ the enhancement of room-temperature thermoelectric power. Physical Review B, 2009, 80, .		
52	Investigation of Paramagnetic Centers in Fullerides A ₂ MC ₆₀ and AM ₂ C ₆₀ (A = K, Rb, M = Mg, Be). Applied Magnetic Resonance, 2008, 33, 177-184.	0.6	1
53	Magnetic anomalies of Na ₃ C ₆₀ . Journal of Physics and Chemistry of Solids, 2008, 69, 1221-1223.	1.9	2
54	Giant improvement of thermoelectric power factor of Bi ₂ Te ₃ under pressure. Journal of Applied Physics, 2008, 104, .	1.1	144

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55	Highly Disordered Crystal Structure and Thermoelectric Properties of Sn_3P_4 . Chemistry of Materials, 2008, 20, 2476-2483.	3.2	48
56	Scattering of carries in InGaAs -doped by Mn InGaAs quantum well with hole-mediated ferromagnetism. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	1
57	Anomalous transport in ferromagnetic $\text{GaAs/In}_x\text{Ga}_{1-x}\text{As/GaAs}$ quantum well δ -doped with Mn and C. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
58	Electronic structure, galvanomagnetic and magnetic properties of the bismuth subhalides Bi_4I_4 and Bi_4Br_4 . Journal of Solid State Chemistry, 2007, 180, 1103-1109.	1.4	36
59	Persistent infrared photoconductivity in InAs/GaAs structures with quantum dot layer. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 39, 1-7.	1.3	2
60	Electronic properties of single-crystal diamonds heavily doped with boron. Journal of Experimental and Theoretical Physics, 2007, 104, 586-589.	0.2	6
61	Thermoelectric properties and ferromagnetism of diluted magnetic semiconductors $\text{Sb}_2\hat{\alpha}^x\text{Cr}_x\text{Te}_3$. Journal of Experimental and Theoretical Physics, 2007, 105, 21-26.	0.2	7
62	Low-temperature transport and ferromagnetism in GaAs -based structures with Mn. Journal of Experimental and Theoretical Physics, 2007, 105, 170-173.	0.2	0
63	Superconductivity and spectroscopy of heterofullerides Rb_2MC_60 , K_2MC_60 , and KM_2C_60 ($M = \text{Mg}, \text{Be}$). Journal of Experimental and Theoretical Physics, 2007, 105, 250-252.	0.2	0
64	New metal-rich mixed chalcogenides with an intergrowth structure: $\text{Ni}_{5.68}\text{SiSe}_2$, $\text{Ni}_{5.46}\text{GeSe}_2$, and $\text{Ni}_{5.42}\text{GeTe}_2$. Russian Chemical Bulletin, 2007, 56, 1694-1700.	0.4	14
65	$\text{Ni}_7\hat{\alpha}^x\text{SnTe}_2$: Modulated crystal structure refinement, electronic structure and anisotropy of electroconductivity. Journal of Solid State Chemistry, 2007, 180, 221-232.	1.4	13
66	Structural and electrophysical properties of pseudomorphic GaAs/InGaAs/GaAs quantum wells: effect of thin central AlAs barrier. , 2006, , .		1
67	Persistent IR photoconductivity in InAs/GaAs structures with QD layers. Semiconductors, 2006, 40, 210-216.	0.2	3
68	Fermi surface and thermoelectric power of $(\text{Bi}_{1-\hat{\alpha}}\text{Sbx})_2\text{Te}_3$ $\langle \text{Ag}, \text{Sn} \rangle$ mixed crystals. Physics of the Solid State, 2006, 48, 833-840.	0.2	10
69	Transport and magnetotransport properties of Mn-doped $\text{In}_x\text{Ga}_{1-\hat{\alpha}}\text{As/GaAs}$ quantum well structures. Journal of Magnetism and Magnetic Materials, 2006, 300, e16-e19.	1.0	6
70	Transport and magnetic properties of Mn- and Mg-implanted GaAs layers. Journal of Magnetism and Magnetic Materials, 2006, 300, e20-e23.	1.0	2
71	Anomalous transport and ferromagnetism in the diluted magnetic semiconductor $\text{Sb}_2\hat{\alpha}^x\text{Cr}_x\text{Te}_3$. Physica B: Condensed Matter, 2005, 368, 32-41.	1.3	16
72	Optical properties of $\text{Hg}_{1-\hat{\alpha}}\text{MnxTe}_{1-\hat{\gamma}}\text{Se}_\gamma$. Infrared Physics and Technology, 2005, 46, 379-387.	1.3	14

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73	Superhard superconducting materials based on diamond and cubic boron nitride. JETP Letters, 2005, 81, 260-263.	0.4	23
74	Anomalous Hall effect and ferromagnetism in the new diluted magnetic semiconductor $Sb_{2-x}Cr_xTe_3$. JETP Letters, 2005, 81, 342-345.	0.4	8
75	Ferromagnetism in a new dilute magnetic semiconductor $Sb_{2-x}Cr_xTe_3$. Journal of Experimental and Theoretical Physics, 2005, 101, 528-534.	0.2	14
76	Specific Features of Photoluminescence of InAs/GaAs QD Structures at Different Pumping Levels. Semiconductors, 2005, 39, 1308.	0.2	3
77	The effect of carrier density gradients on magnetotransport data measured in Hall bar geometry. Solid State Communications, 2004, 130, 705-710.	0.9	13
78	Fullerides: heterometallic superconductors with composition $M_2M'C_6O$ ($M = K, Rb; M' = Yb, Lu, Sc$). Russian Chemical Bulletin, 2004, 53, 1686-1692.	0.4	8
79	Thermoelectric power and Shubnikov-de Haas effect in magnetic impurity-doped Bi_2Te_3 and Bi_2Se_3 . Journal of Magnetism and Magnetic Materials, 2004, 272-276, 1991-1992.	1.0	18
80	Heterometallic fullerides of Fe and Cu groups with the composition $K_2M'C_6O$ ($M = Fe^{+2}, Fe^{+3}, Co^{+2}$). Russian Chemical Bulletin, 2004, 53, 1693-1697.	0.9	21
81	2D metal slabs in new nickel-tin chalcogenides Ni_7-xSnQ_2 ($Q = Se, Te$): average crystal and electronic structures, chemical bonding and physical properties. Journal of Solid State Chemistry, 2004, 177, 3616-3625.	1.4	22
82	Low temperature ferromagnetism in the new diluted magnetic semiconductor $p-Bi_{2-x}Fe_xTe_3$. Physica B: Condensed Matter, 2003, 329-333, 1251-1252.	1.3	9
83	Magnetic-field-induced quantum Hall insulator transition and persistent photoconductivity in InAs/GaAs quantum dot layers. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 159-160.	1.3	1
84	Peculiarities of conductivity in structures delta-doped by Si on vicinal (111)A GaAs substrate. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 172-173.	1.3	0
85	Peculiarities of the electron transport in very short period InAs/GaAs superlattices near quantum dot formation. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 300-302.	1.3	0
86	Magnetic-field-induced quantum Hall effect Hall insulator transition and hopping conductivity in InAs/GaAs quantum dot layers. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 18, 116-117.	1.3	1
87	Persistent photoconductivity in quantum dot layers in InAs/GaAs structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1297-1300.	0.8	4
88	Effect of electron irradiation on the galvanomagnetic properties of $In_xBi_{2-x}Te_3$ semiconductor single crystals. Physics of the Solid State, 2003, 45, 2249-2254.	0.2	5
89	A tunneling spectroscopy study of the temperature dependence of the forbidden band in Bi_2Te_3 and Sb_2Te_3 . Journal of Experimental and Theoretical Physics, 2003, 97, 1212-1218.	0.2	18
90	Optical and electronic properties of tin quantum wires formed on vicinal surface of GaAs. Journal of Experimental and Theoretical Physics, 2002, 97, 4762, 99.		0

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91	Influence of Sn on Galvanomagnetic Properties of Layered p-(Bi _{1-x} Sb _x) ₂ Te ₃ Semiconductors. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 1467-1480.	0.7	32
92	Ferromagnetism in new diluted magnetic semiconductor Bi _{2-x} FexTe ₃ . <i>Physica B: Condensed Matter</i> , 2002, 311, 292-297.	1.3	92
93	Electron paramagnetic resonance studies of Hg _{1-x} Mn _x Te _{1-x} Se _x . <i>Solid State Communications</i> , 2002, 122, 389-393.	0.9	6
94	Ferromagnetic transition in the new diluted magnetic semiconductor p-Bi _{2-x} FexTe ₃ . <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2001, 285, 173-176.	0.9	15
95	A new type of quantized Hall effect in layered semiconductors Bi _{2-x} Sn _x Te ₃ and Sb _{2-x} Sn _x Te ₃ . <i>Physica B: Condensed Matter</i> , 2001, 298, 510-514.	1.3	8
96	A new type of bulk quantum Hall effect in Bi _{2-x} SnxTe ₃ crystals. <i>Physica B: Condensed Matter</i> , 2000, 284-288, 1718-1719.	1.3	4
97	Kinetic Properties of Current Carriers in GICs and Low Density Carbon Materials. <i>Molecular Crystals and Liquid Crystals</i> , 2000, 340, 247-252.	0.3	0
98	Cyclotron Resonance in High Magnetic Fields in Bi ₂ Se ₃ , Bi ₂ Te ₃ and Sb ₂ Te ₃ Based Crystals. <i>Journal of the Physical Society of Japan</i> , 1999, 68, 3328-3333.	0.7	22
99	Peculiarities of optical and low-temperature transport properties of multi-layer InAs/GaAs structures with quantum dots. <i>Physica B: Condensed Matter</i> , 1999, 266, 185-191.	1.3	4
100	Conducting wires embedded in an i-GaAs matrix for electronic applications. <i>Microelectronic Engineering</i> , 1998, 43-44, 319-324.	1.1	1
101	Low temperature transport properties of InAs/GaAs structures with quantum dots. <i>Microelectronic Engineering</i> , 1998, 43-44, 107-111.	1.1	3
102	Magnetotransport in GaAs δ -doped by Sn. <i>Physica B: Condensed Matter</i> , 1998, 256-258, 243-247.	1.3	7
103	Synthesis of Fullerides of Alkali and Alkali-Earth Metals under Mechanical and Chemical Activation. <i>Molecular Crystals and Liquid Crystals</i> , 1998, 310, 149-154.	0.3	5
104	The Enhancement of Thermoelectric Power and Scattering of Carriers in Bi _{2-x} SnxTe ₃ Single Crystals. <i>Materials Research Society Symposia Proceedings</i> , 1997, 478, 133.	0.1	0
105	Quenching of persistent photoconductivity and decrease of electron concentration by high electric fields in GaAs δ -doped by Sn on vicinal substrate structures. <i>Physica B: Condensed Matter</i> , 1997, 229, 262-267.	1.3	6
106	Thermoelectric Power and Scattering of Carriers in Bi _{2-x} SnxTe ₃ with Layered Structure. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 199, 505-513.	0.7	27
107	Low temperature subband 2D electron mobilities in heavy δ - and modulation doped GaAs/GaAlAs heterostructures. <i>European Physical Journal D</i> , 1996, 46, 2457-2458.	0.4	0
108	Low temperature negative magnetoresistance in the δ -doped by Sn and Si on vicinal and singular substrates GaAs structures. <i>European Physical Journal D</i> , 1996, 46, 2513-2514.	0.4	0

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109	Galvanomagnetic properties of low density foils fabricated from exfoliated graphite. Journal of Physics and Chemistry of Solids, 1996, 57, 893-897.	1.9	6
110	Influence of pressure on the energy spectrum of low stage graphite intercalation compounds. Journal of Physics and Chemistry of Solids, 1996, 57, 943-946.	1.9	0
111	Time decay of thermoremanent magnetization in cluster-glass phase of intercalation compound Fe_xTiS_2 studied by use of anomalous Hall effect. Journal of Magnetism and Magnetic Materials, 1995, 145, 157-164.	1.0	5
112	Quantum corrections to conductivity and quantum hall effect in GaAs-GaAlAs multiple quantum well structures. Physica B: Condensed Matter, 1994, 194-196, 1197-1198.	1.3	0
113	Magnetic properties of diluted $(\text{Zn}_{1-x}\text{Mn}_x)_3\text{As}_2$ solutions. Solid State Communications, 1992, 84, 531-535.	0.9	5
114	Superconductivity in lithium intercalated 2H-NbSe_2 . Synthetic Metals, 1991, 42, 1925-1928.	2.1	2
115	Shubnikov-de Haas effect in graphite intercalation compounds superlattices. Synthetic Metals, 1991, 42, 2693-2696.	2.1	1
116	Coexistence of 2D weak localization and superconductivity in carbon fibers. Synthetic Metals, 1991, 42, 2697-2700.	2.1	3
117	Energy spectrum of Bi_2Te_3 intercalated by Li and Ba. Physica B: Condensed Matter, 1991, 173, 303-304.	1.3	3
118	Localization and negative magnetoresistance in Si-MOSFET. Solid State Communications, 1990, 76, 1135-1138.	0.9	1
119	Drift resonance in the quantum hall effect. Solid State Communications, 1990, 73, 583-588.	0.9	7
120	Tunneling spectroscopy of band edge structures of Bi/Te and Sb/Te . , 0, , .		2
121	Tunneling spectroscopy of electronic structures of $\text{Bi}/\text{Sn}/\text{Te}$. , 0, , .		0
122	Thermoelectric properties of mixed layered compounds TiS_2 and Se . , 0, , .		1
123	Calculation of Carrier Scattering and Negative Magnetoresistance in Mn-Doped GaAs/InGaAs/GaAs Quantum Well with Ferromagnetism. Solid State Phenomena, 0, 152-153, 283-286.	0.3	1
124	Ferromagnetism in GaAs/InAs/GaAs Quantum Dot Layer Delta-Doped with Mn. Solid State Phenomena, 0, 233-234, 93-96.	0.3	0